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June 2014

FDMC86240

N-Channel Shielded Gate PowerTrench[®] MOSFET 150 V, 16 A, 51 m Ω

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)} = 51 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$, $I_D = 4.6 \text{ A}$
- Max $r_{DS(on)} = 70 \text{ m}\Omega$ at $V_{GS} = 6 \text{ V}$, $I_D = 3.9 \text{ A}$
- Low Profile 1 mm max in Power 33
- 100% UIL Tested
- RoHS Compliant



General Description

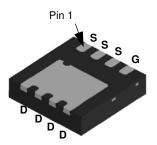
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance.

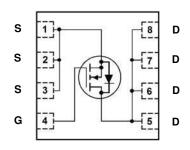
Application

■ DC - DC Conversion

Top Bottom







MLP 3.3x3.3

MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V _{DS}	Drain to Source Voltage			150	V
V_{GS}	Gate to Source Voltage			±20	V
	Drain Current -Continuous	T _C = 25 °C		16	
I _D	-Continuous	T _A = 25 °C	(Note 1a)	4.6	Α
	-Pulsed			20	
E _{AS}	Single Pulse Avalanche Energy		(Note 3)	34	mJ
В	Power Dissipation	T _C = 25 °C		40	W
P_{D}	Power Dissipation	T _A = 25 °C	(Note 1a)	2.3	VV
T _J , T _{STG}	Operating and Storage Junction Temperatu	ıre Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case		3.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note	e 1a)	53	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC86240	FDMC86240	Power 33	13 "	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	150			V
$\Delta BV_{DSS} \ \Delta T_{J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		101		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 120 V, V _{GS} = 0 V			1	μΑ
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2.0	2.9	4.0	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$, referenced to 25 °C		-9		mV/°C
		$V_{GS} = 10 \text{ V}, I_D = 4.6 \text{ A}$		44.7	51	
r _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 6 \text{ V}, I_D = 3.9 \text{ A}$		51.4	70	mΩ
		$V_{GS} = 10 \text{ V}, I_D = 4.6 \text{ A}, T_J = 125 ^{\circ}\text{C}$		84.5	97	
9 _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_D = 4.6 \text{ A}$		15		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 75 V V 0 V	680	905	pF
Coss	Output Capacitance	V _{DS} = 75 V, V _{GS} = 0 V, f = 1 MHz	79	105	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1011 12	4.3	10	pF
R _q	Gate Resistance		0.5		Ω

Switching Characteristics

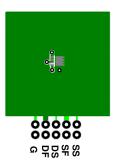
$t_{d(on)}$	Turn-On Delay Time		8.2	17	ns
t _r	Rise Time	$V_{DD} = 75 \text{ V}, I_D = 4.6 \text{ A},$	1.7	10	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_{GEN} = 6 Ω	14	26	ns
t _f	Fall Time		3.1	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V _{GS} = 0 V to 10 V	11	15	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to 5 V}$ $V_{DD} = 75 \text{ V},$ $I_{D} = 4.6 \text{ A}$	6	9	nC
Q_{gs}	Total Gate Charge	1 _D = 4.6 A	2.8		nC
Q_{gd}	Gate to Drain "Miller" Charge		2.3		nC

Drain-Source Diode Characteristics

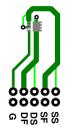
V _{SD} Source to Drain Diode Forward Voltage	Source to Drain Diode, Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 4.6 \text{ A}$	(Note 2)	0.79	1.3	V
	$V_{GS} = 0 \text{ V}, I_{S} = 2 \text{ A}$	(Note 2)	0.75	1.2	v	
t _{rr}	Reverse Recovery Time	I _F = 4.6 A, di/dt = 100 A/μs		58	93	ns
Q _{rr}	Reverse Recovery Charge			63	102	nC

NOTES

^{1.} R_{BJA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design.



53 °C/W when mounted on a 1 in² pad of 2 oz copper



125 °C/W when mounted on a minimum pad of 2 oz copper

^{2.} Pulse Test: Pulse Width < 300 $\mu\text{s},$ Duty cycle < 2.0%.

^{3.} Starting T $_{J}$ = 25 °C; N-ch: L = 3 mH, I $_{AS}$ = 4.8 A, V $_{DD}$ = 150 V, V $_{GS}$ = 10 V.

Typical Characteristics T_J = 25 °C unless otherwise noted

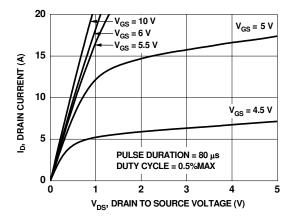


Figure 1. On-Region Characteristics

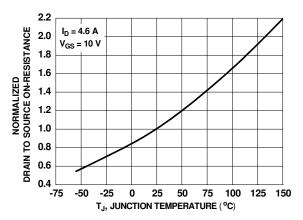


Figure 3. Normalized On-Resistance vs. Junction Temperature

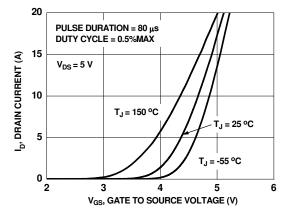


Figure 5. Transfer Characteristics

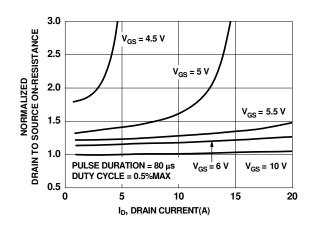


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

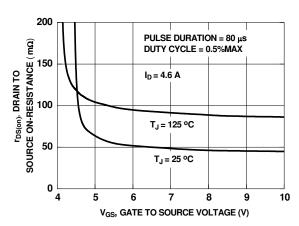


Figure 4. On-Resistance vs. Gate to Source Voltage

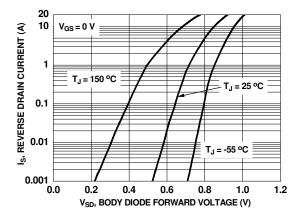


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics $T_J = 25$ °C unless otherwise noted

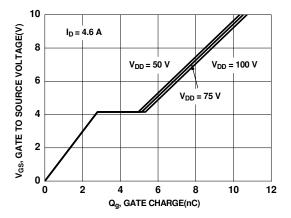


Figure 7. Gate Charge Characteristics

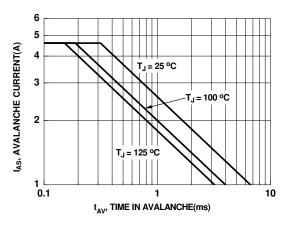


Figure 9. Unclamped Inductive Switching Capability

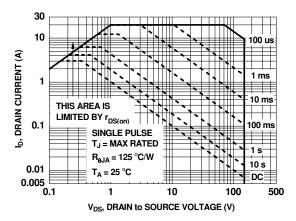


Figure 11. Forward Bias Safe Operating Area

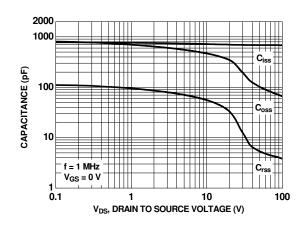


Figure 8. Capacitance vs. Drain to Source Voltage

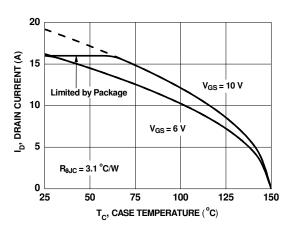


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

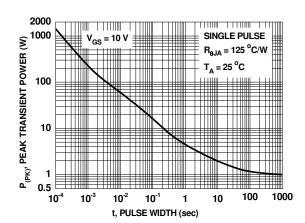


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25$ °C unless otherwise noted

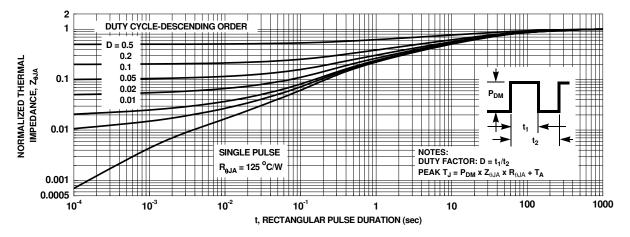
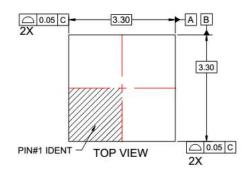
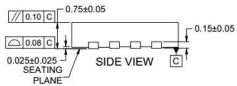
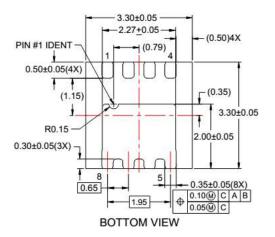


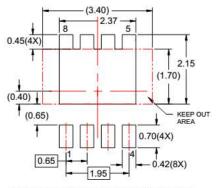
Figure 13. Transient Thermal Response Curve

Dimensional Outline and Pad Layout









RECOMMENDED LAND PATTERN

NOTES:

- A. DOES NOT CONFORM TO JEDEC REGISTRATION MO-229
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- E. DRAWING FILENAME: MKT-MLP08Srev3.



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